

Inventor: Janos Fucsko et al.

Title: Wet Etching Method of Removing Silicon From a Substrate and
Method of Forming Trench Isolation

Assignee: Micron Technology, Inc.

INFORMATION DISCLOSURE STATEMENT

References -- See Attached Form PTO-1449

The attached form PTO-1449 is submitted in compliance with
37 CFR § 1.56. Copies of the cited art are included. No admission is made
regarding whether all the submitted references are prior art.

Respectfully submitted,

Dated: 7-22-03

Attorney: 

Mark S. Matkin
Reg. No. 32,268

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-2246		SERIAL NO. Unknown	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT: Janos Fucsko et al.			
				FILING DATE Filed Herewith		GROUP Unknown	
U.S. PATENT DOCUMENTS							
*Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
	AJ						
	AK						
	AL						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
	AM		Bertagna et al., <i>Ionic components dependence of the charge transfer reactions at the silicon / HF solution</i> <i>Interface</i> , 4 J. SOLID STATE ELECTROCHEM. 42-51 (1999).				
	AN						
	AO						
EXAMINER		DATE CONSIDERED					
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>							